

JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	(p) PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

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PTO/SB/08A (08-00)

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		First Named Inventor	Ning
		Group Art Unit	TBD
Examiner Name	TBD		
Attorney Docket Number	01-P-18264 US		

J1040 U.S. PTO  
 10/05/02  
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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	✓	KAR-ROY, ARJUN, HU, CHUN, RACANELLI, MARCO, COMPTON, CORY A., KEMPF, PAUL, JOLLY, GURVINDER, SHERMAN, PHIL N., ZHENG, JIE, ZHANG, ZHE and YIN, AIGUO, "High Density Metal Insulator Metal Capacitors Using PECVD Nitride for Mixed Signal and RF Circuits", IEEE, 1999, IITC 99-245-247.	
	✓	LIU, RUICHEN, LIN, CHENG-YIH, HARRIS, EDWARD, MERCHANT, SAILESH, DOWNEY, STEPHEN W., WEBER, GARY, CIAMPA, NICHOLAS A., TAI WAI, LAI, WARREN, Y. C., MORRIS, MARK D., BOWER, J. ERIC, MINER, JOHN F., FRACKOVIAK, JOHN, MANSFIELD, WILLIAM, BARR, DAVID, KELLER, ROBERT, CHANG, CHONG-PING, PAI, CHIEN-SHING, ROGERS, SARA N. AND GREGOR, RICHARD, "Single Mask Metal-Insulator-Metal (MIM) Capacitor with Copper Damascene Metallization for Sub-0.18µm Mixed Mode Signal and System-on-a-Chip (SoC) Applications", IEEE, 2000, pp. 111-113.	
	✓	ARMACOST, M., AUGUSTIN, A., FELSNER, P., FEND, Y., FRIESE, G., HEIDENREICH, J., HUECKEL, G., PRIGGE, O., STEIN, K., "A High Reliability Metal Insulator Metal Capacitor for 0.18 µm Copper Technology", 4 pages.	

Examiner Signature	<i>B. Talbot</i>	Date Considered	4/25/03
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